

Serial No. 10/627,893

IN THE SPECIFICATION:

On page 4, please add the following new paragraph after paragraph 0008:

-- **Figure 5** shows a block diagram of a system in accordance with some embodiments of the invention. --

Please replace paragraph [0023] on page 11 with the following paragraph:

--[0023] An embodiment 300 of the present invention is shown in **Figure 3** illustrating a polymer/P-N junction memory device. With reference to **Figure 3**, one or more polymer memory data elements are indicated at a polymer/LED 324 array. A vacuum shroud 326 and an end cap 312 form a closed container (a high vacuum environment) in which electron beam source 314 emits e-beam 120, incident upon the polymer/LED 324 array. Control electronics 310 may be used in conjunction with the electron beam source 314 as needed to control the e-beam source. The e-beam 120 may be steered by means of electron lens 316 and deflection electrodes 318. --

Please replace paragraph 0030 on page 14 with the following new paragraphs:

--[0030] With reference to Fig. 5, some embodiments of a system 500 may include a data storage device 501 (e.g. as described above), a processor 502 coupled with the data storage device 501, a system bus 503 coupled with the processor 502, and a data storage device controller 504 to control data transfer between the data storage device 501 and the processor 502. For example, some embodiments may further include a display 505 coupled with the system bus 503.

Serial No. 10/627,893

[0031] Thus, a novel solution to electron beam recording and sensing of data bits is disclosed. Although the invention is described herein with reference to specific preferred embodiments, many modifications therein will readily occur to those of ordinary skill in the art. Accordingly, all such variations and modifications are included within the intended scope of the invention as defined by the following claims. —